

T410H

High temperature 4 A sensitive TRIACs

Features

- Medium current TRIAC
- Logic level sensitive TRIAC
- 150 °C max. T_i turn-off commutation
- Clip bounding
- RoHS (2002/95/EC) compliant package

Applications

- The T410H is designed for the control of AC actuators in appliances and industrial systems.
- The multi-port drive of the microcontroller can control the multiple loads of such appliances and systems through this sensitive gate TRIAC.

Description

Specifically designed to operate at 150 °C, the new 4 A T410H TRIAC provides an enhanced performance in terms of power loss and thermal dissipation. This allows the optimization of the heatsink size, leading to space and cost effectiveness when compared to electromechanical solutions.

Based on ST logic level technology, the T410H offers an I_{GT} lower than 10 mA and specified minimal commutation and high noise immunity levels valid up to the T_i max.

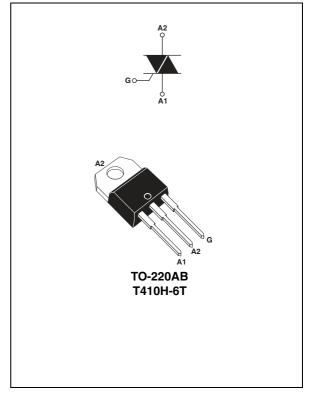


Table 1.	Device	summary
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Symbol	Value	Unit
I _{T(RMS)}	4	А
V _{DRM} /V _{RRM}	600	V
I _{GT MAX}	10	mA

1 Characteristics

Symbol	I Parameter			Value	Unit
I _{T(RMS)}	On-state rms current (full sine wave) $T_c = 141 \text{ °C}$		4	А	
	Non repetitive surge peak on-state current	F = 60 Hz	t = 16.7 ms	42	А
ITSM	(full quale T initial OF 90)	F = 50 Hz	t = 20 ms	40	A
l ² t	I ² t Value for fusing	t _p = 10 ms	1	11	A ² s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \ x \ I_{GT}$, $t_r \leq 100 \ ns$	F = 120 Hz	T _j = 150 °C	50	A/µs
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage	t _p = 10 ms	T _j = 25 °C	V _{DRM} /V _{RRM} + 100	V
I _{GM}	Peak gate current $t_p = 20 \ \mu s$ T		T _j = 150 °C	4	А
P _{G(AV)}	Average gate power dissipation $T_j = 150 \text{ °C}$		1	W	
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 150	°C

Table 2. Absolute maximum ratings

Table 3.Electrical characteristics (T_i = 25 °C, unless otherwise specified)

Symbol	Test conditions	Quadrant	Min.	Max.	Unit
I _{GT}		1 - 11 - 111	1	10	mA
V _{GT}	$V_D = 12 V R_L = 33 \Omega$	- -		1.0	V
V_{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$	- -	0.15		V
I _H ⁽¹⁾	^{I)} I _T = 100 mA			25	mA
I		1 - 111		30	
۱ _L	$I_{G} = 1.2 I_{GT}$	II		35	– mA
dV/dt ⁽¹⁾	dV/dt ⁽¹⁾ $V_D = 67\% V_{DRM}$, gate open, $T_j = 150 \text{ °C}$		75		V/µs
(dl/dt)c ⁽¹⁾	Logic level, 0.1 V/ μ s, T _j = 150 °C		5.7		A/ms
(ui/ut)C (*/	Logic level, 15 V/ μ s, T _j = 150 °C		1.5		A/ms

1. For both polarities of A2 referenced to A1.



Table 4.	Static characteristics					
Symbol	Test conditions			Value	Unit	
$V_{T}^{(1)}$	$I_{TM} = 5.6 \text{ A}, t_p = 380 \ \mu \text{s}$	T _j = 25 °C	MAX.	1.5	V	
V _{t0} ⁽¹⁾	Threshold voltage	T _j = 150 °C	MAX.	0.80	V	
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	MAX.	80.0	mΩ	
	<u> </u>	T _j = 25 °C	MAX.	5	μA	
I _{DRM}	$V_{DRM} = V_{RRM}$	T _j = 150 °C	MAX.	2.2		
I _{RRM}	$V_D/V_R = 400 V$ (at peak mains voltage)	T _j = 150 °C	MAX.	1.75	mA	
	$V_D/V_R = 200 V$ (at peak mains voltage)	T _j = 150 °C	MAX.	1.5		

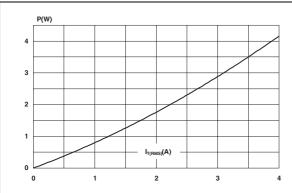
Table 4.Static characteristics

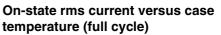
1. for both polarities of A2 referenced to A1.

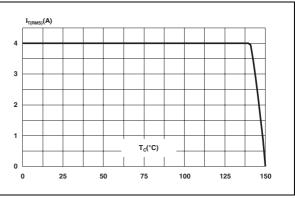
Table 5.Thermal resistance

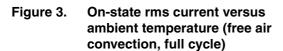
Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	2.20	°C/W
R _{th(j-a)}	Junction to ambient	60	0/10

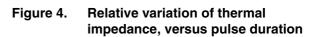
Figure 1. Maximum power dissipation versus Figure 2. on-state rms current (full cycle)

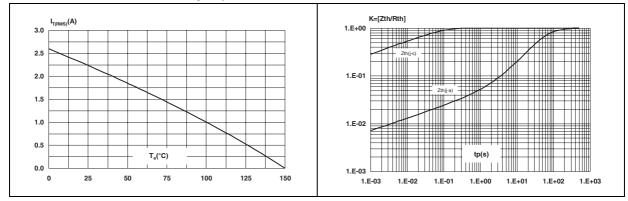




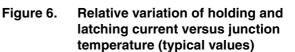












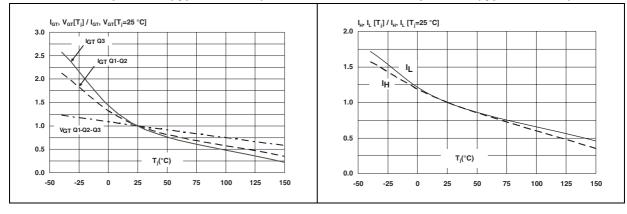
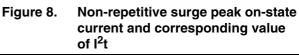


Figure 7. Surge peak on-state current versus number of cycles



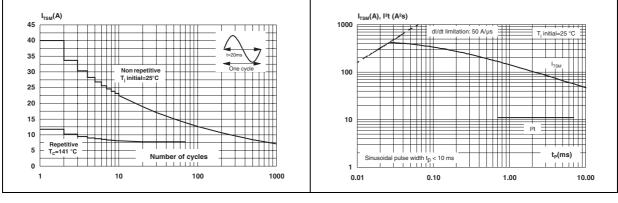
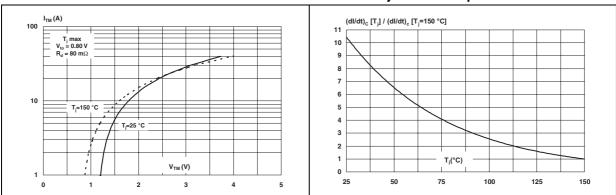


Figure 9. On-state characteristics (maximum values)

Figure 10. Relative variation of critical rate of decrease of main current versus junction temperature





Relative variation of critical rate of Figure 12. Relative variation of static dV/dt Figure 11. decrease of main current versus immunity versus junction reapplied dV/dt (typical values) temperature

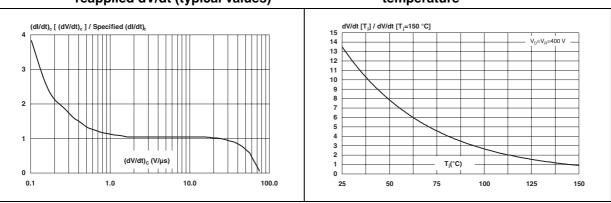
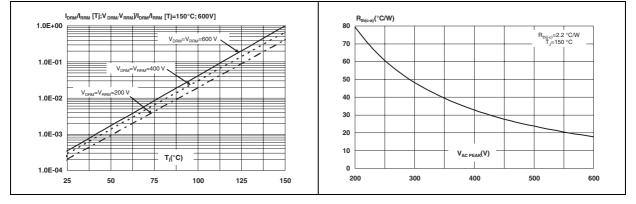


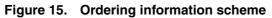
Figure 13. Variation of leakage current versus Figure 14. Acceptable case to ambient thermal junction temperature for different values of blocking voltage

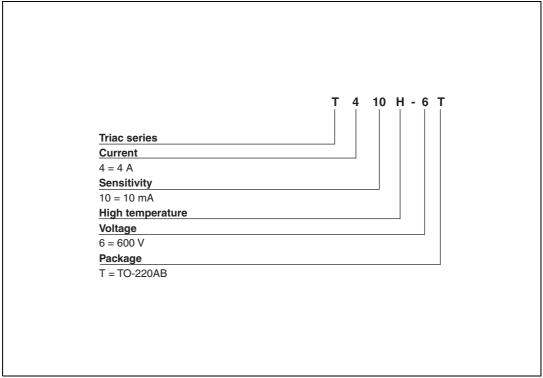
resistance versus repetitive peak off-state voltage





2 Ordering information scheme





3 Package information

- Epoxy meets UL94, V0
- Recommended torque 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK[®] is an ST trademark.

Table 6. TO-220AB dimensions

			Dimensions					
		Ref.	Mi	illimete	rs		Inches	
	-		Min.	Тур.	Max.	Min.	Тур.	Max.
		А	15.20		15.90	0.598		0.625
		a1		3.75			0.147	
	, C	a2	13.00		14.00	0.511		0.551
	<u>2</u>	В	10.00		10.40	0.393		0.409
		b1	0.61		0.88	0.024		0.034
A		b2	1.23		1.32	0.048		0.051
14 13	c2 ↔	С	4.40		4.60	0.173		0.181
		c1	0.49		0.70	0.019		0.027
		c2	2.40		2.72	0.094		0.107
		е	2.40		2.70	0.094		0.106
	M ← c1	F	6.20		6.60	0.244		0.259
_{fe} ⊧	→H≪	ØI	3.75		3.85	0.147		0.151
		14	15.80	16.40	16.80	0.622	0.646	0.661
		L	2.65		2.95	0.104		0.116
		12	1.14		1.70	0.044		0.066
		13	1.14		1.70	0.044		0.066
		М		2.60			0.102	



4 Ordering information

Table 7.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T410H-6T	T410H 6T	TO-220AB	2.3 g	50	Tube

5 Revision history

Table 8.Document revision history

Date	Revision	Changes
15-May-2009	1	First issue.



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Doc ID 15712 Rev 1